

Supporting Information

One-Dimensional TeSe Nano-Heterojunction: Formation, Calculations, Carrier Dynamics, and Application in Broad-Spectrum Photodetectors

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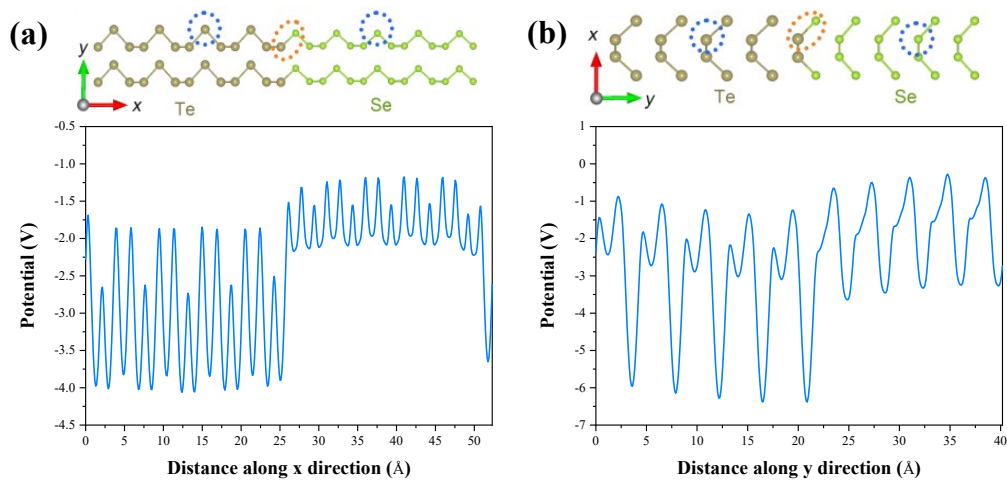


Figure R1 Electrostatic potential of the Se/Te heterostructures along different directions: **(a)** x direction and **(b)** y direction, respectively.

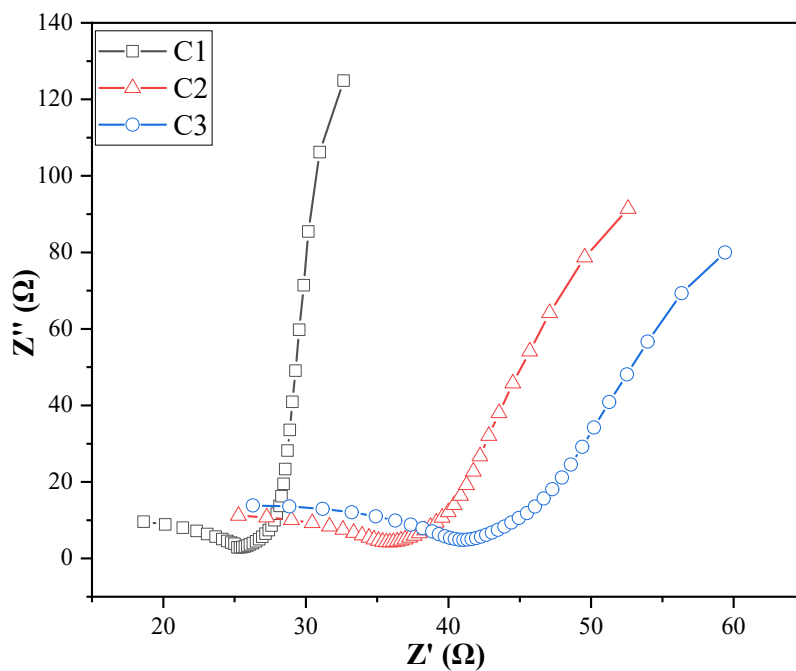


Figure S2 Electrochemical impedance spectrum (EIS) of TeSe PDs in seawater with various concentrations under illumination by simulated light at 0.6 V.